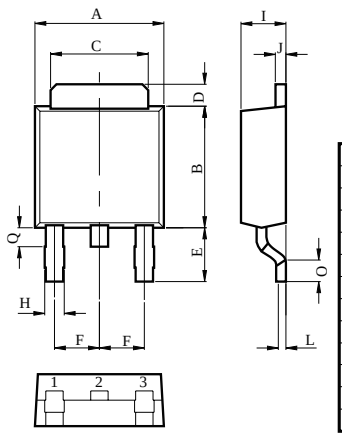
FTD1899 TRANSISTOR (NPN)

FEATURES

- Low $V_{CE(sat)}$
- High Transition Frequency



DIM	MILLIMETERS
A	6 50 ± 0 2
B	5 60 ± 0 2
C	5 20 ± 0 2
D	1 50 ± 0 2
E	2 70 ± 0 2
F	2 30 ± 0 1
H	1 00 MAX
I	2 30 ± 0 2
J	0 5 ± 0 1
L	0 50 ± 0 10
O	1 6 ± 0 2
Q	0 95 MAX

1 BASE
2 COLLECTOR
3 EMITTER

DPAK

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current	3	A
P_C	Collector Power Dissipation	1	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	125	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA,I_E=0	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA,I_C=0	7			V
Collector cut-off current	I_{CBO}	V_{CB}=60V,I_E=0			10	μA
Emitter cut-off current	I_{EBO}	V_{EB}=7V,I_C=0			10	μA
DC current gain	$h_{FE(1)}$*	V_{CE}=2V, I_C=0.2A	60			
	$h_{FE(2)}$*	V_{CE}=2V, I_C=0.6A	100		400	
	$h_{FE(3)}$*	V_{CE}=2V, I_C=2A	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$*	I_C=1.5A,I_B=0.15A			0.25	V
Base-emitter saturation voltage	$V_{BE(sat)}$*	I_C=1.5A,I_B=0.15A			1.2	V
Collector output capacitance	C_{ob}	V_{CB}=10V,I_E=0, f=1MHz		30		pF
Transition frequency	f_T	V_{CE}=5V,I_C=1.5A		120		MHz

*Pulse test: pulse width ≤350μs, duty cycle≤ 2.0%.

CLASSIFICATION OF $h_{FE(2)}$

RANK	M	L	K
RANGE	100-200	160-320	200-400

Typical Characteristics